

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_F(AV)$	1 A
V_{RRM}	40 V
$V_F(max)$	0.5 V

FEATURES AND BENEFITS

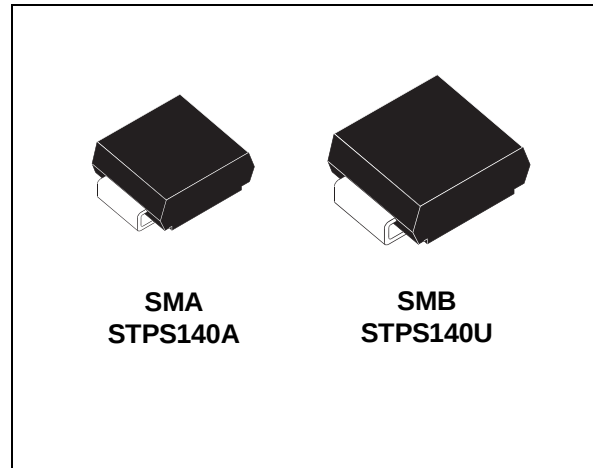
- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNTED DEVICE

DESCRIPTION

Single chip Schottky rectifier suited for Switch-mode Power Supplies and high frequency DC to DC converters.

Packaged in SMA and SMB(*), this device is intended for surface mounting and used in low voltage, high frequency inverters, free wheeling and polarity protection applications.

(*) in accordance with DO214AA and DO21AC JEDEC



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			40	V
$I_F(RMS)$	RMS forward current			7	A
$I_F(AV)$	Average forward current $\delta = 0.5$	SMA	$T_L = 130^\circ C$	1	A
		SMB	$T_L = 135^\circ C$		
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ Sinusoidal		60	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2\text{ }\mu s$ $F = 1\text{ kHz}$		1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100\text{ }\mu s$ square		1	A
T_{stg}	Storage temperature range			- 65 to + 150	$^\circ C$
T_j	Maximum junction temperature			150	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μs

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-l)}$	Junction to lead	SMA	30	$^{\circ}\text{C/W}$
		SMB	25	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = 40\text{V}$		12	μA
		$T_j = 100^{\circ}\text{C}$		0.25	2	mA
V_F^{**}	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 1\text{A}$		0.55	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 1\text{A}$	0.43	0.5	
		$T_j = 25^{\circ}\text{C}$	$I_F = 2\text{A}$		0.65	
		$T_j = 125^{\circ}\text{C}$	$I_F = 2\text{A}$	0.53	0.6	

Pulse test : * $t_p = 5\text{ms}$, $\delta < 2\%$
 ** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.4 \times I_{F(AV)} + 0.10 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

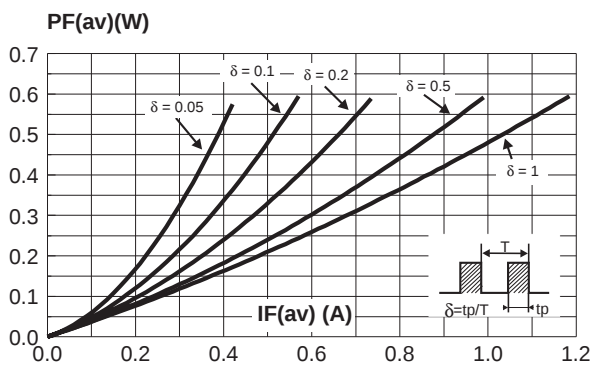


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

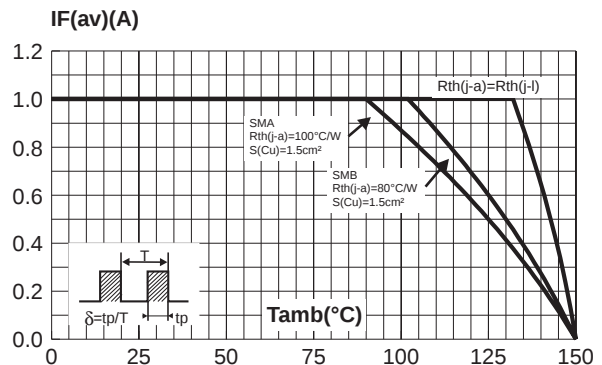


Fig. 3-1: Non repetitivesurge peak forward current versus overload duration (maximum values) (SMB).

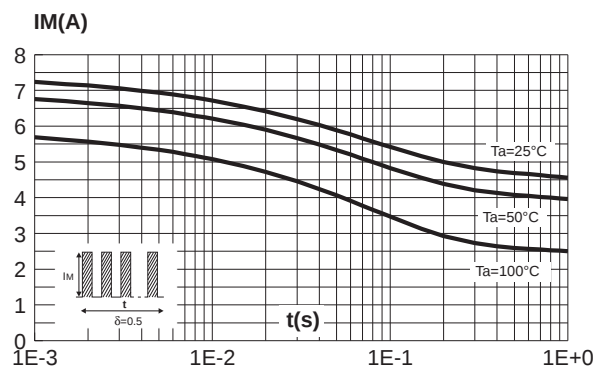


Fig. 3-2: Non repetitivesurge peak forward current versus overload duration (maximum values) (SMA).

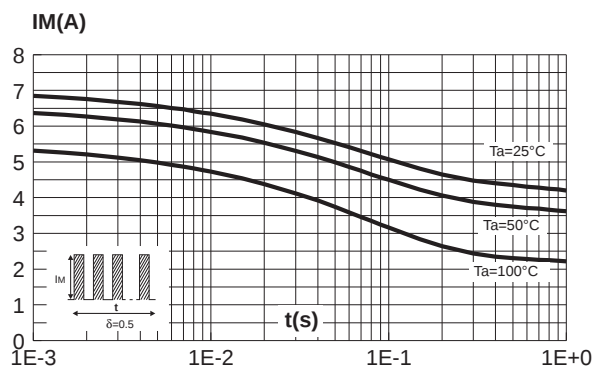


Fig. 4-1: Relative variation of thermal impedance junction to ambient versus pulse duration (SMB).

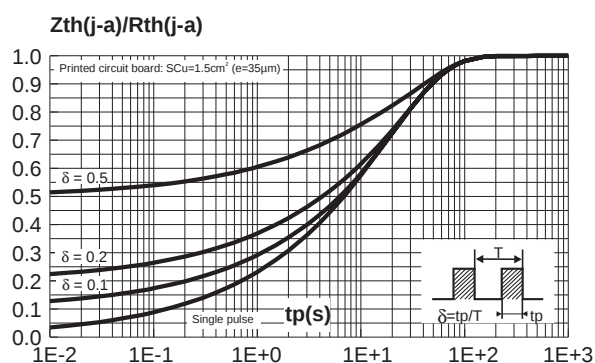


Fig. 4-2: Relative variation of thermal impedance junction to ambient versus pulse duration (SMA).

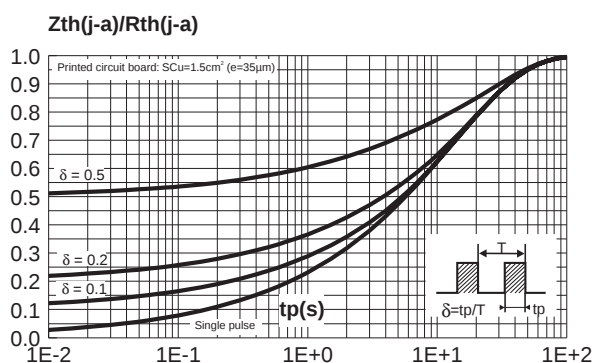


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

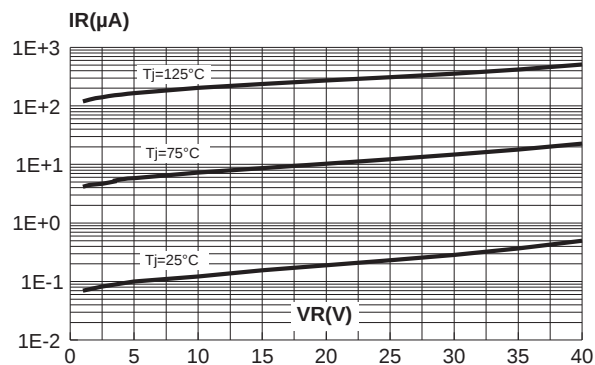


Fig. 6: Junction capacitance versus reverse voltage applied (typical values)

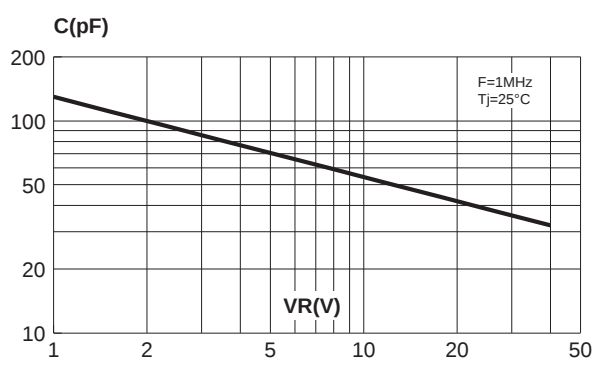


Fig. 7: Forward voltage drop versus forward current (maximum values).

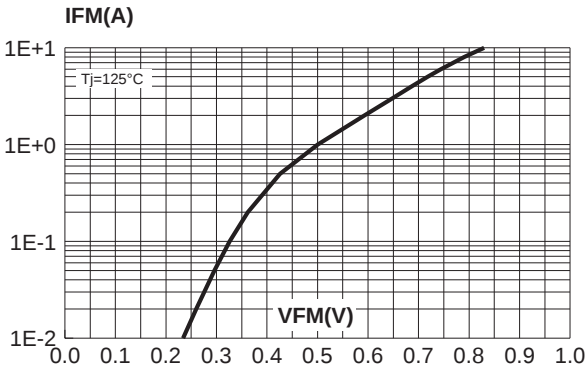


Fig. 8-1: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board, copper thickness: 35μm)(SMB).

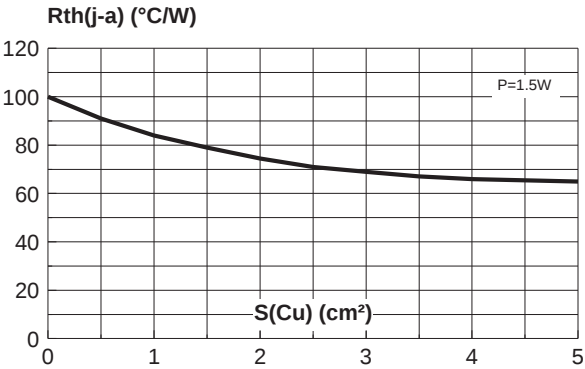
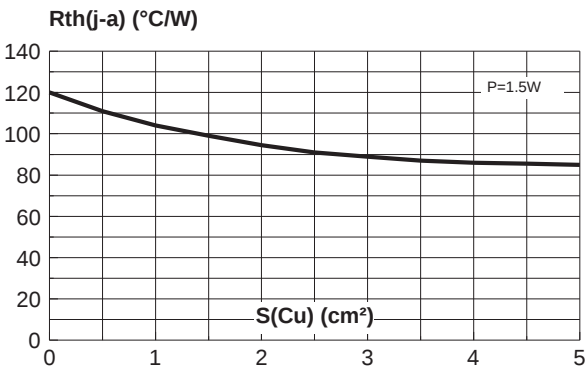


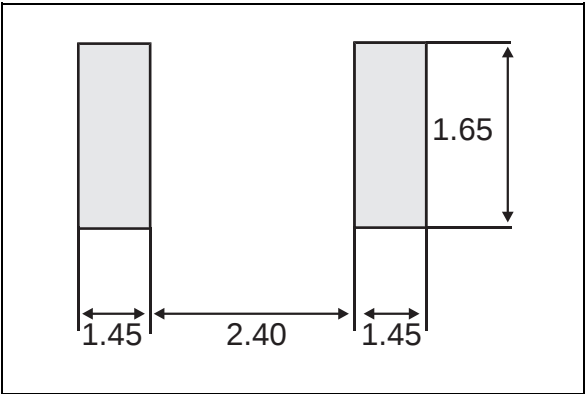
Fig. 8-2: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board, copper thickness: 35μm)(SMA).



PACKAGE MECHANICAL DATA
SMA

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.70	0.075	0.106
A2	0.05	0.20	0.002	0.008
b	1.25	1.65	0.049	0.065
c	0.15	0.41	0.006	0.016
E	4.80	5.60	0.189	0.220
E1	3.95	4.60	0.156	0.181
D	2.25	2.95	0.089	0.116
L	0.75	1.60	0.030	0.063

FOOT PRINT (in millimeters)



■ Marking: S140

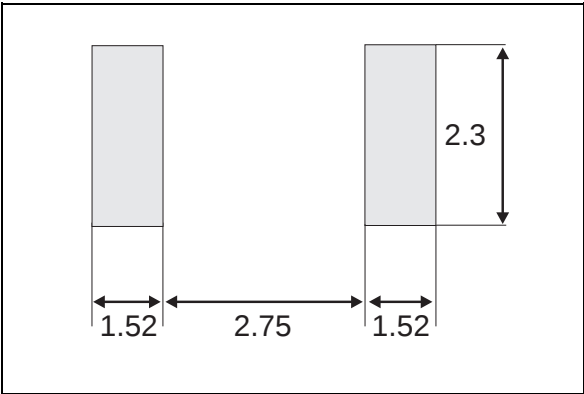
STPS140A/U

PACKAGE MECHANICAL DATA
SMB Plastic

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.41	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

FOOT PRINT (in millimeters)

■ Marking: G14



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